

N-CHANNEL MOSFET Qualified per MIL-PRF-19500/592

DEVICES

2N7225 2N7225U

LEVELS

**JAN
 JANTX
 JANTXV**

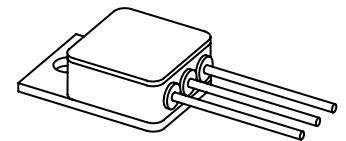
ABSOLUTE MAXIMUM RATINGS ($T_C = +25^\circ\text{C}$ unless otherwise noted)

Parameters / Test Conditions	Symbol	Value	Unit
Drain – Source Voltage	V_{DS}	200	Vdc
Gate – Source Voltage	V_{GS}	± 20	Vdc
Continuous Drain Current $T_C = +25^\circ\text{C}$	I_{D1}	27.4	A _{dc}
Continuous Drain Current $T_C = +100^\circ\text{C}$	I_{D2}	17	A _{dc}
Max. Power Dissipation $T_C = +25^\circ\text{C}$	P_{tl}	150 ⁽¹⁾	W
Drain to Source On State Resistance	$R_{ds(on)}$	0.1 ⁽²⁾	Ω
Operating & Storage Temperature	T_{op}, T_{stg}	-55 to +150	$^\circ\text{C}$

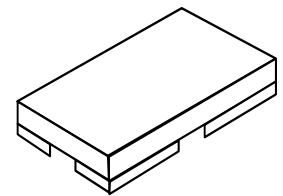
Note: (1) Derated Linearly by 1.2 W/ $^\circ\text{C}$ for $T_C > +25^\circ\text{C}$
 (2) $V_{GS} = 10\text{Vdc}$, $I_D = 17\text{A}$

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Drain-Source Breakdown Voltage $V_{GS} = 0\text{V}$, $I_D = 1\text{mA}$	$V_{(BR)DSS}$	200		Vdc
Gate-Source Voltage (Threshold) $V_{DS} \geq V_{GS}$, $I_D = 0.25\text{mA}$ $V_{DS} \geq V_{GS}$, $I_D = 0.25\text{mA}$, $T_j = +125^\circ\text{C}$ $V_{DS} \geq V_{GS}$, $I_D = 0.25\text{mA}$, $T_j = -55^\circ\text{C}$	$V_{GS(th)1}$ $V_{GS(th)2}$ $V_{GS(th)3}$	2.0 1.0	4.0 5.0	Vdc
Gate Current $V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$ $V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$, $T_j = +125^\circ\text{C}$	I_{GSS1} I_{GSS2}		± 100 ± 200	nA _{dc}
Drain Current $V_{GS} = 0\text{V}$, $V_{DS} = 160\text{V}$ $V_{GS} = 0\text{V}$, $V_{DS} = 160\text{V}$, $T_j = +125^\circ\text{C}$	I_{DSS1} I_{DSS2}		25 0.25	μA _{dc} mA _{dc}
Static Drain-Source On-State Resistance $V_{GS} = 10\text{V}$, $I_D = 17\text{A}$ pulsed $V_{GS} = 10\text{V}$, $I_D = 27.4\text{A}$ pulsed $T_j = +125^\circ\text{C}$ $V_{GS} = 10\text{V}$, $I_D = 17\text{A}$ pulsed	$r_{DS(on)1}$ $r_{DS(on)2}$ $r_{DS(on)3}$		0.100 0.105 0.17	Ω Ω Ω
Diode Forward Voltage $V_{GS} = 0\text{V}$, $I_D = 27.4\text{A}$ pulsed	V_{SD}		1.9	Vdc



TO-254AA



**U-PKG (U3)
 TO-276AB**



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TECHNICAL DATA SHEET

N-CHANNEL MOSFET Qualified per MIL-PRF-19500/592

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Gate Charge:				
On-State Gate Charge	$Q_{g(on)}$		115	nC
Gate to Source Charge	Q_{gs}		22	
Gate to Drain Charge	Q_{gd}		60	
$V_{GS} = 10V, I_D = 27.4A$ $V_{DS} = 50V$				

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Switching time tests:				
Turn-on delay time	$t_{d(on)}$		35	ns
Rinse time	t_r		190	
Turn-off delay time	$t_{d(off)}$		170	
Fall time	t_f		130	
Diode Reverse Recovery Time	t_{rr}		950	ns
$I_D = 27.4A, V_{GS} = 10Vdc,$ Gate drive impedance = $7.5\Omega,$ $V_{DD} = 100Vdc$				
$di/dt \leq 100A/\mu s, V_{DD} \leq 30V,$ $I_F = 27.4A$				